

Figure 1: Dielectric data (permittivity (ε<sub>r</sub>) and loss (tanδ)) of ALD 100nm Al<sub>2</sub>O<sub>3</sub> deposited onto platinized silicon, p-type and n-type low resistivity silicon, and MLD 80nm alucone capped with 20nm Al<sub>2</sub>O<sub>3</sub> on platinized silicon